TOSHIBA

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type ( $\pi$ -MOSVII)

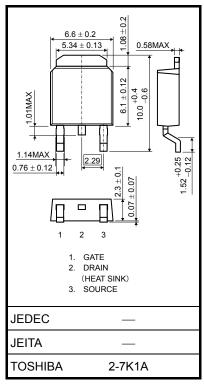
# TK4P55DA

#### Switching Regulator Applications

- Low drain-source ON-resistance: RDS (ON) = 2.0  $\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 1.8 \text{ S}$  (typ.)
- Low leakage current:  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 550 \ V)$
- Enhancement mode:  $V_{th} = 2.4$  to 4.4 V ( $V_{DS} = 10$  V,  $I_D = 1$  mA)

Characte	ristics	Symbol	Rating	Unit			
Drain-source voltage		V <sub>DSS</sub>	550	V			
Gate-source voltage		V <sub>GSS</sub>	±30	V			
Drain current	DC (Note 1)	ID	3.5				
	Pulse (t = 1 ms) (Note 1)	I <sub>DP</sub>	14	A			
Drain power dissipati	on (Tc = 25°C)	PD	80	W			
Single pulse avalanche energy (Note 2)		E <sub>AS</sub>	121	mJ			
Avalanche current		I <sub>AR</sub>	3.5	А			
Repetitive avalanche	energy (Note 3)	E <sub>AR</sub>	8	mJ			
Channel temperature		T <sub>ch</sub>	150	°C			
Storage temperature range		T <sub>stg</sub>	-55 to 150	°C			

#### Absolute Maximum Ratings (Ta = 25°C)



Weight: 0.36 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

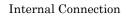
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R <sub>th (ch-c)</sub>	1.56	°C/W
Thermal resistance, channel to ambient	R <sub>th (ch-a)</sub>	125	°C/W

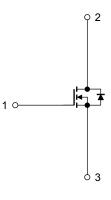
Note 1:Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD} = 90 \text{ V}, \text{ T}_{ch} = 25^{\circ}\text{C}(\text{initial}), \text{ L} = 17.1 \text{ mH}, \text{ R}_{G} = 25 \Omega, \text{ I}_{AR} = 3.5 \text{ A}$ 

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.





Start of commercial production 2009-12

Unit: mm

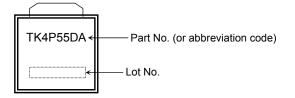
**Electrical Characteristics (Ta = 25°C)** 

Char	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS}=\pm 30~V,~V_{DS}=0~V$	_		±1	μA
Drain cut-off current		I <sub>DSS</sub>	$V_{DS} = 550 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	_		10	μA
Drain-source bre	akdown voltage	V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	550			V
Gate threshold v	oltage	V <sub>th</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	2.4		4.4	V
Drain-source ON	-resistance	R <sub>DS (ON)</sub>	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 1.8 \text{ A}$	_	2.0	2.45	Ω
Forward transfer	admittance	Y <sub>fs</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1.8 \text{ A}$	0.4	1.8	_	S
Input capacitance		C <sub>iss</sub>		_	380	—	pF
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS}$ = 25 V, $V_{GS}$ = 0 V, f = 1 MHz	_	2.5	—	
Output capacitance		C <sub>oss</sub>			45	_	
Switching time	Rise time	tr	$10 V$ $V_{GS}$ $0 V$ $50 \Omega$ $K_{L} = 111 \Omega$ $V_{DD} \approx 200 V$	_	15		ns
	Turn-on time	t <sub>on</sub>			35	_	
	Fall time	t <sub>f</sub>			7	_	
	Turn-off time	t <sub>off</sub>	Duty $\leq$ 1%, $t_W^{}=$ 10 $\mu s$	_	55	_	
Total gate charge		Qg			9		
Gate-source charge		Q <sub>gs</sub>	$V_{DD}\approx 400$ V, $V_{GS}=10$ V, $I_{D}=3.5$ A	_	5		nC
Gate-drain charge		Q <sub>gd</sub>	]	_	4	_	

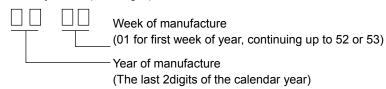
## Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>	—	_	_	3.5	A
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	—	_	_	14	А
Forward voltage (diode)	V <sub>DSF</sub>	$I_{DR} = 3.5 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	-1.7	V
Reverse recovery time	t <sub>rr</sub>	$I_{DR} = 3.5 \text{ A}, V_{GS} = 0 \text{ V},$	_	800	_	ns
Reverse recovery charge	Q <sub>rr</sub>	dl <sub>DR</sub> /dt = 100 A/μs	_	4.4	_	μC

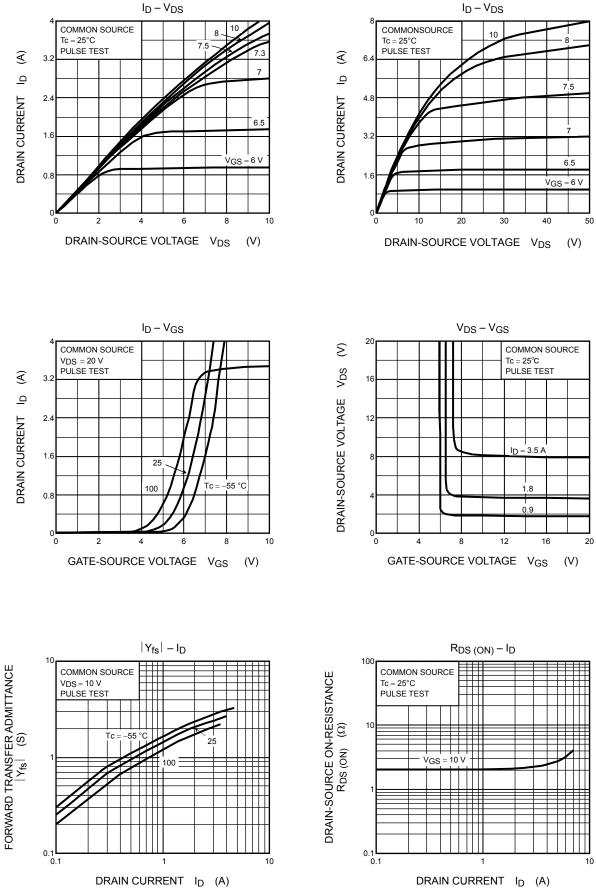
## Marking(Note 4)



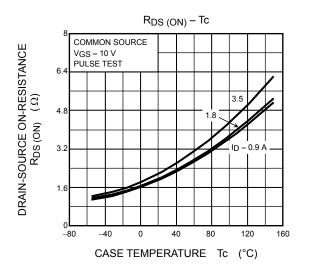
Note 4: \* Weekly code: (Four digits)

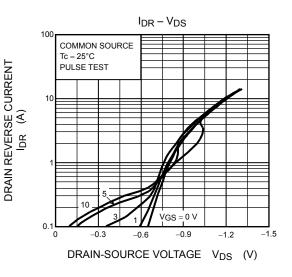


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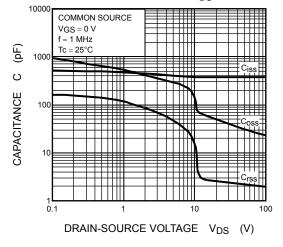


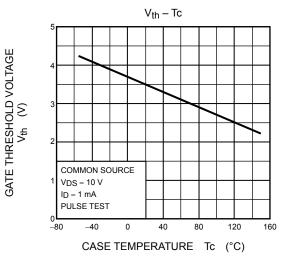
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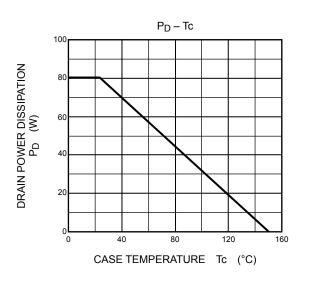


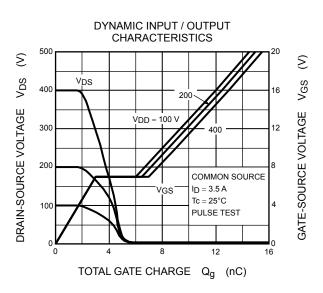


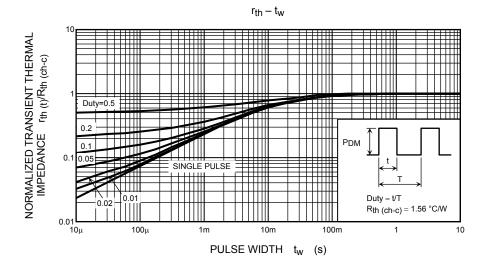
CAPACITANCE – V<sub>DS</sub>

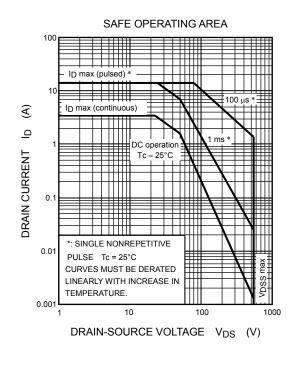


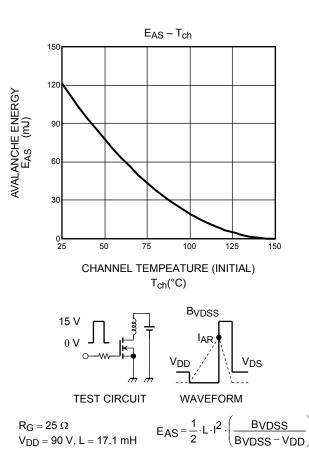












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